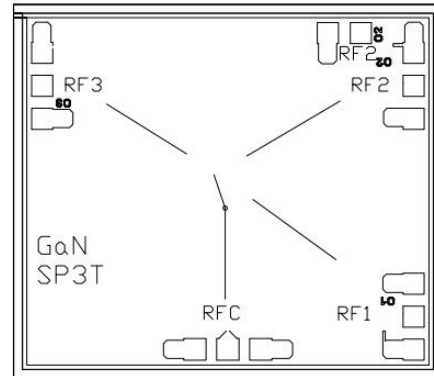


Performance

- Technology: 0.25um GaN FET
- Frequency: 0.1~3GHz
- Insertion loss: 0.8dB
- Isolation: 40dB
- Input P-0.3: 51dBm
- Input/Output VSWR: 1.4:1
- Switching Time: 20ns
- Control Mode: 0/-40V
- Voltage control reflective switch
- Chip size: 1.95*1.7*0.08mm

Function Diagram



Electrical Specifications (Ta=+25°C, V1~V2=0V/-40V, F=0.1~3GHz)

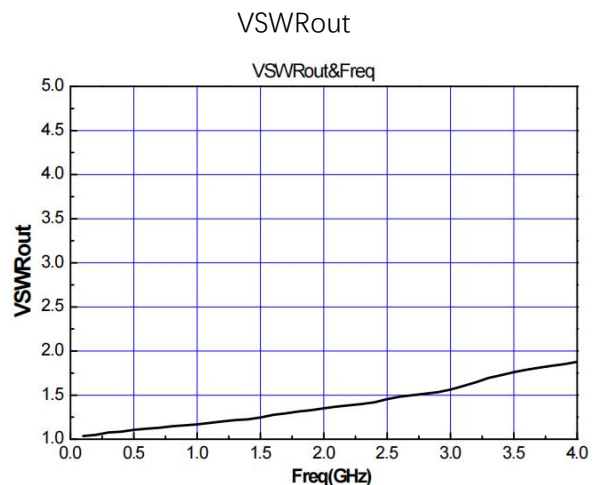
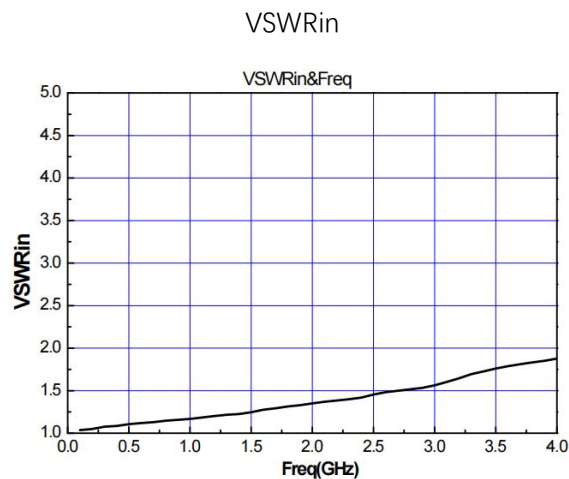
Symbol	Parameter	Min.	Typ.	Max.	Unit
Li	Insertion Loss	-	0.8	-	dB
ISO	Isolation	-	40	-	dB
VSWR	Input / Output VSWR	-	1.4	-	-

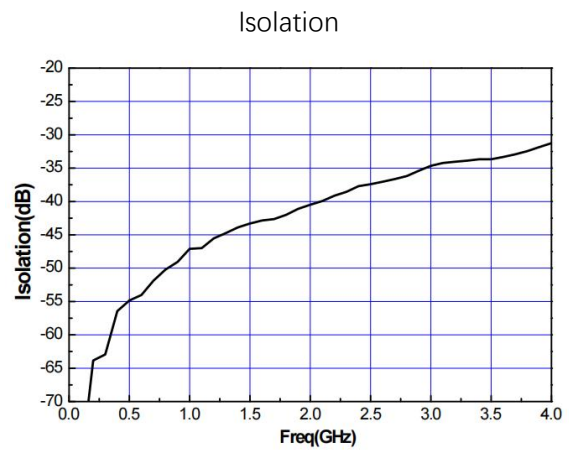
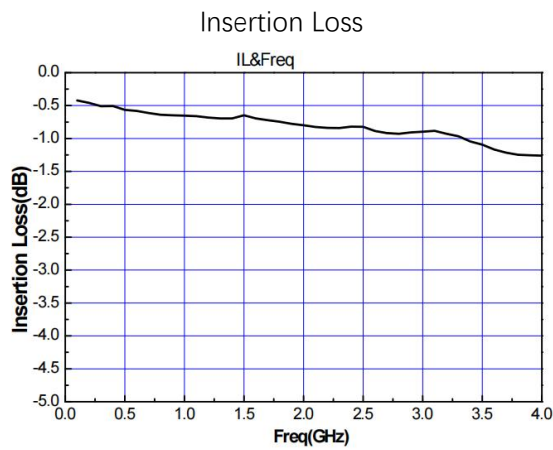
Absolute Maximum Ratings (Ta=+25°C)

Symbol	Parameter	Value	Notes
V1,2	Control Voltage	-60V	
Pcw	Input Continuous Wave Power	52dBm	
Tch	Channel Temperature	225°C	
T	Sintering Temperature	310°C	30s, N2 protection
Tstg	Storage Temperature	-55~150°C	

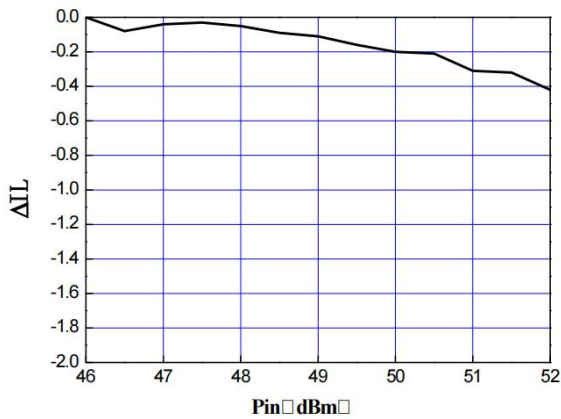
Exceed any of above listed ratings may cause permanent damage.

Test Curves (Ta=+25°C, (V1,2=-40V))

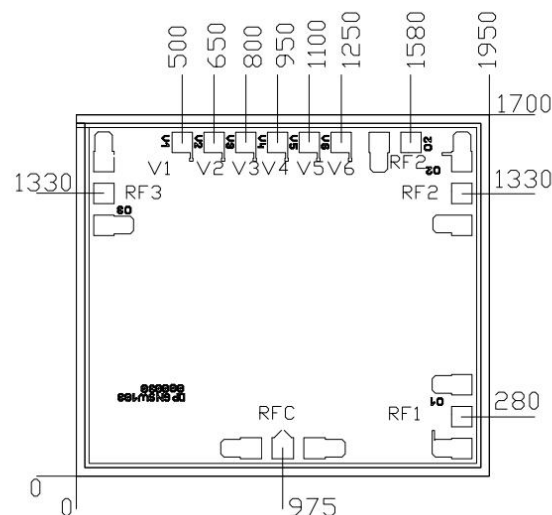




Input Power (Y axis is normalized value of I.L)



Outline Size (μm)



Note: 1. Recommended single wire length for RF port is $>0.8\text{mm}$, $<1.2\text{mm}$.

Dual wires length is $>1\text{mm}$, $<1.5\text{mm}$.

2. Choose one of RF2.

PIN Definition

PIN	Description
RF1、RF2、RF2	RF ports, 50Ω
RFc	RF common ports, 50Ω
V1、V2、V3、V4、V5、V6	Control Ports
GND	Bottom must be grounded

Truth Table

V1	V2	V3	V4	V5	V6	RF _c →RF ₁	RF _c →RF ₂	RF _c →RF ₃
0	1	0	1	0	1	OFF	OFF	OFF
1	0	0	1	0	1	OFF	OFF	ON
0	1	1	0	0	1	OFF	ON	OFF
0	1	0	1	1	0	ON	OFF	OFF

Note: Low level "0" is -28V~-40V, High level "1" is 0V~0.5V